



# DOCUMENT CHANGE REQUEST

DCR number	1183	Changes required for:	General	Originator:	Aissa Nehdi
Date:	2019/07/04	Date sent:	2018/10/15	Organisation:	STMicroelectronics
Status:	IMPLEMENTED				

Title: Transistors High Power NPN, based on type 2N5154

Number: 5203/010 Issue: 7

Other documents affected:

Page:

11

Paragraph:

Paragraph : 1.7.2

Original wording:

new dimension for TO257 and SMD.5 package

Proposed wording:

new dimension for TO257 and SMD.5 package

Justification:

new dimension for TO257 and SMD.5 package

Attachments:

5204002iss7(3).pdf, 5203010iss7(3).pdf, 5203010\_draft(3).pdf, modification\_for\_4\_escs\_specification\_of\_detail(3).docx, 5203016iss4(3).pdf

Modifications:

-TO 257: D dimension shall be 4.7 min & 5.33 max (OK for both process) and J max at 3.18  
-SMD 5 : A dimension shall be 2.84 min & 3.30 max ( OK for both process)

Approval signature:

Date signed:

2019-07-04

